
2SC460, 2SC461

Silicon NPN Epitaxial Planar

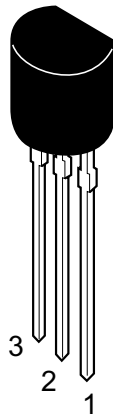
HITACHI

Application

- 2SC460 high frequency amplifier, mixer
- 2SC461 VHF amplifier, mixer

Outline

TO-92 (2)



1. Emitter
2. Collector
3. Base

2SC460, 2SC461

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Item	Symbol	2SC460	2SC461	Unit
Collector to base voltage	V_{CBO}	30	30	V
Collector to emitter voltage	V_{CEO}	30	30	V
Emitter to base voltage	V_{EBO}	5	5	V
Collector current	I_{C}	100	100	mA
Collector power dissipation	P_{C}	200	200	mW
Junction temperature	T_{j}	150	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	-55 to +150	$^\circ\text{C}$

Electrical Characteristics (Ta = 25°C)

Item	Symbol	2SC460			2SC461			Unit	Test conditions
		Min	Typ	Max	Min	Typ	Max		
Collector to base breakdown voltage	$V_{(BR)CBO}$	30	—	—	30	—	—	V	$I_C = 10 \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	30	—	—	30	—	—	V	$I_C = 1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	—	—	5	—	—	V	$I_E = 10 \mu A, I_C = 0$
Collector cutoff current	I_{CBO}	—	—	0.5	—	—	0.5	μA	$V_{CB} = 18 \text{ V}, I_E = 0$
Emitter cutoff current	I_{EBO}	—	—	0.5	—	—	0.5	μA	$V_{EB} = 2 \text{ V}, I_C = 0$
Base to emitter voltage	V_{BE}	—	0.63	0.75	—	0.63	0.75	V	$V_{CE} = 12 \text{ V}, I_C = 2 \text{ mA}$
DC current transfer ratio	h_{FE}^{*1}	35	—	200	35	—	200		$V_{CE} = 12 \text{ V}, I_C = 2 \text{ mA}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	0.6	1.1	—	0.6	1.1	V	$I_C = 10 \text{ mA}, I_B = 1 \text{ mA}$
Gain bandwidth product	f_T	—	230	—	—	230	—	MHz	$V_{CE} = 12 \text{ V}, I_C = 2 \text{ mA}$
Collector output capacitance	C_{ob}	—	1.8	3.5	—	1.8	3.5	pF	$V_{CB} = 10 \text{ V}, I_E = 0,$ $f = 1 \text{ MHz}$
10.7 MHz power gain	PG	26	29	—	—	—	—	dB	$V_{CE} = 6 \text{ V}, I_E = -1 \text{ mA}$ $f = 10.7 \text{ MHz}$
100 MHz power gain	PG	—	—	—	13	17	—	dB	$V_{CE} = 6 \text{ V}, I_E = -1 \text{ mA}$ $f = 100 \text{ MHz}$
Noise figure	NF	—	2.0	—	—	—	—	dB	$V_{CE} = 6 \text{ V}, I_E = -1 \text{ mA}$ $f = 1 \text{ MHz}$ $R_g = 500 \Omega$

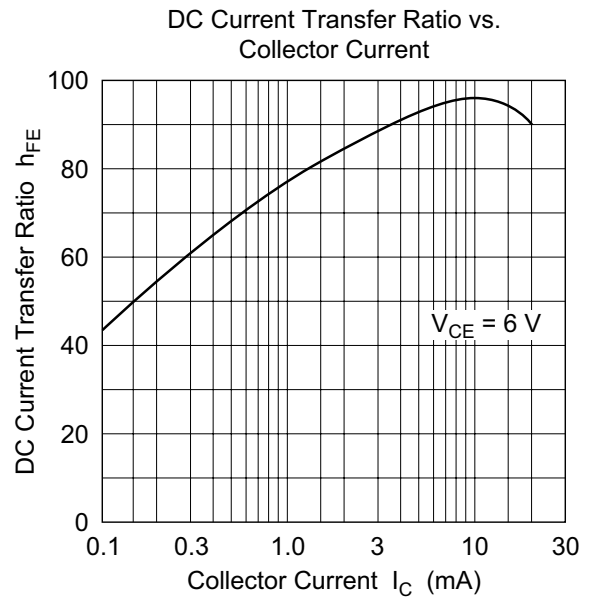
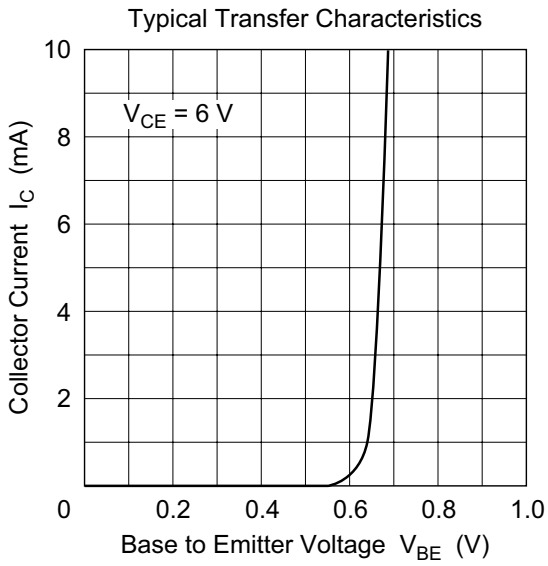
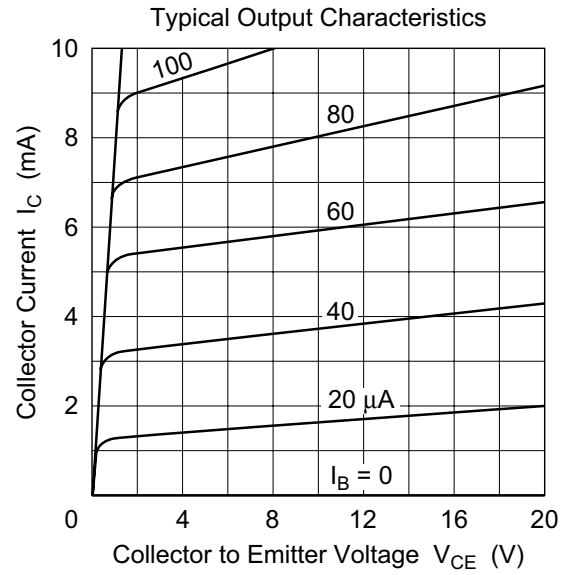
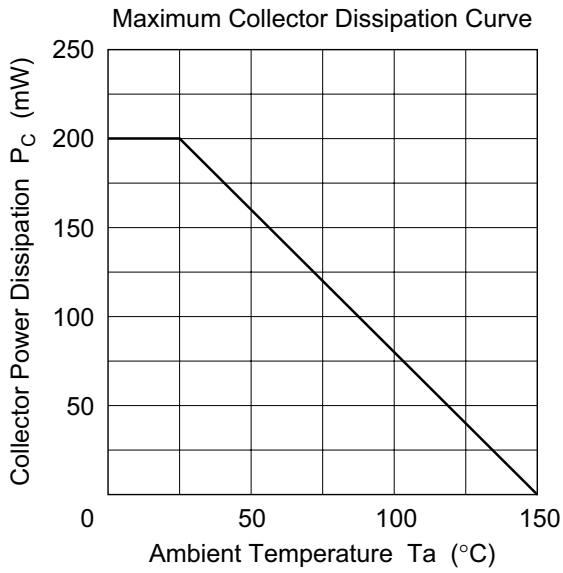
Note: 1. The 2SC460 and 2SC461 are grouped by h_{FE} as follows.

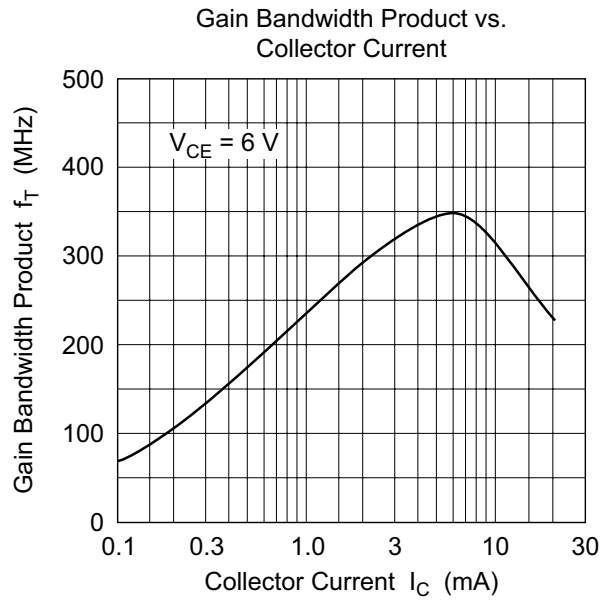
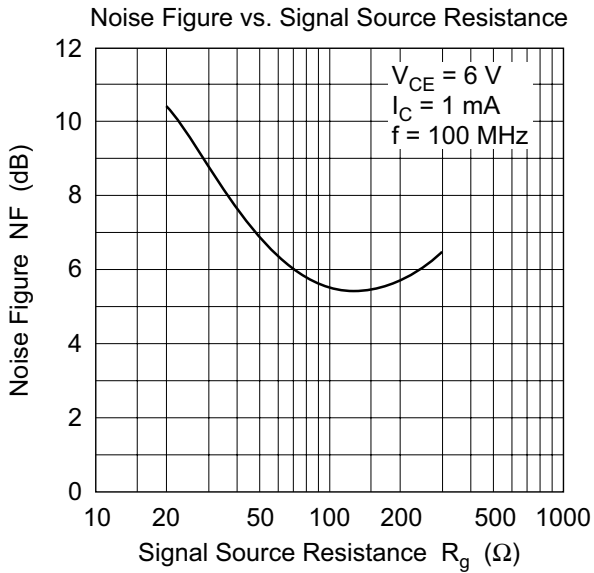
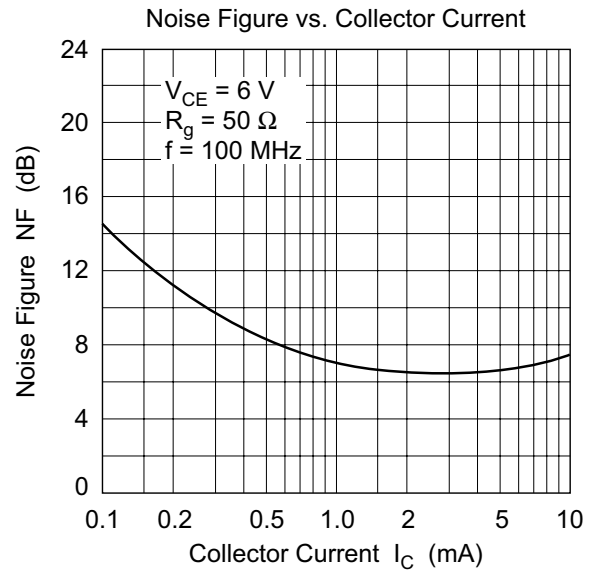
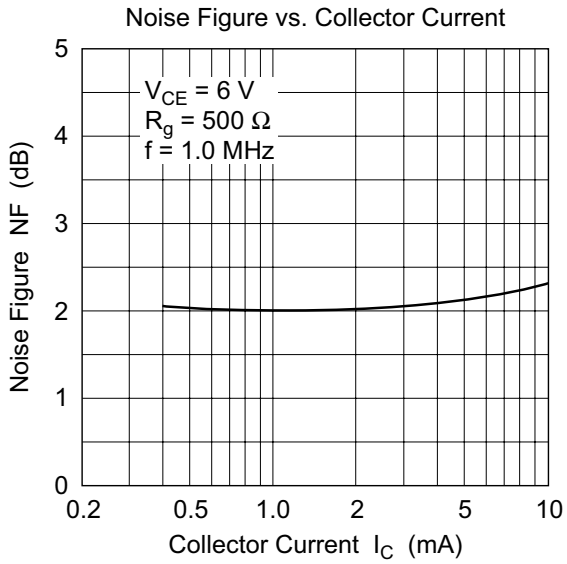
A	B	C
35 to 70	60 to 120	100 to 200

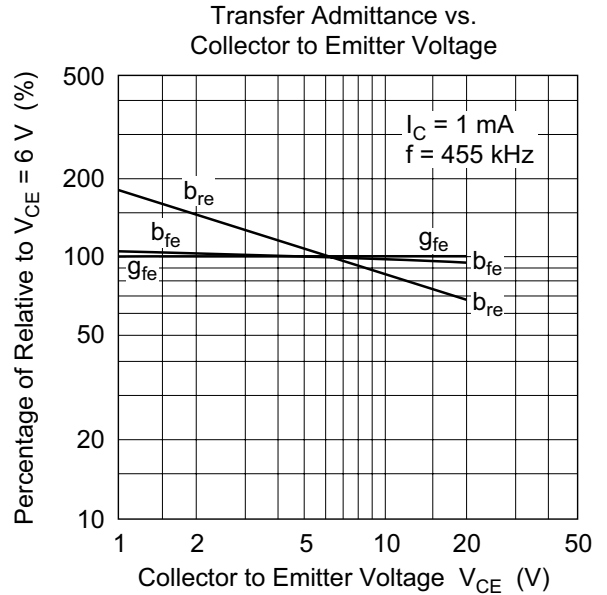
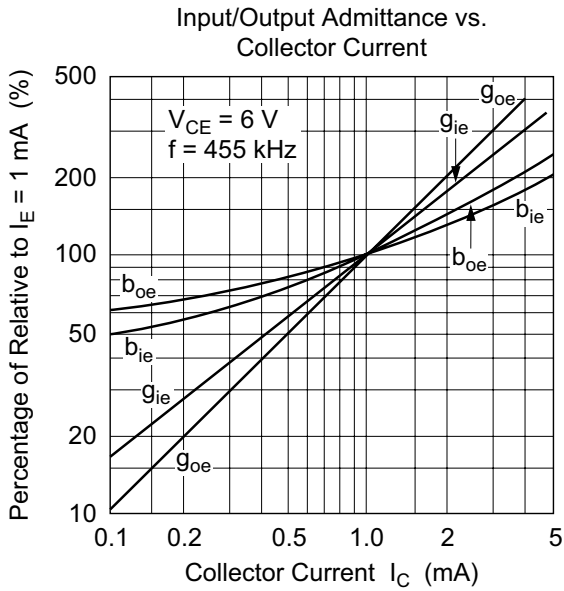
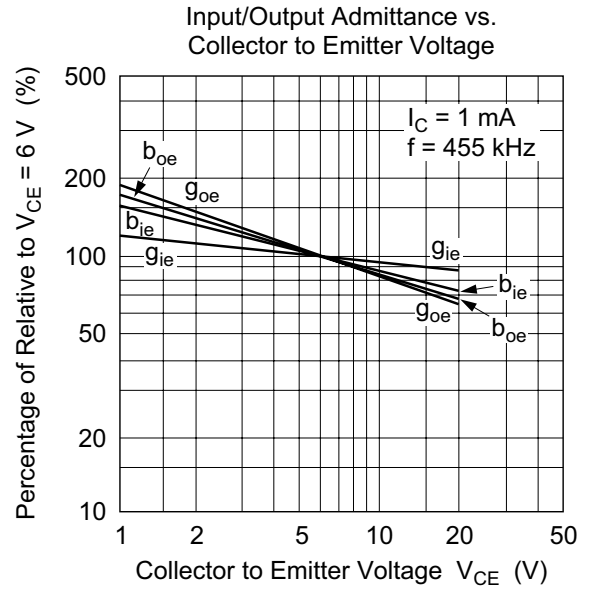
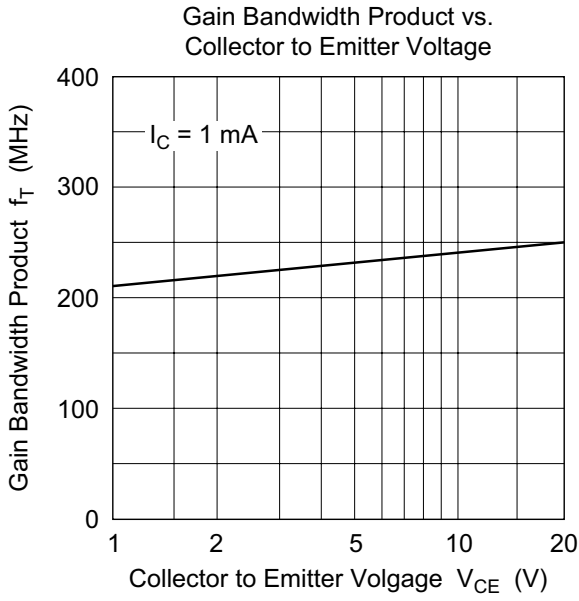
2SC460, 2SC461

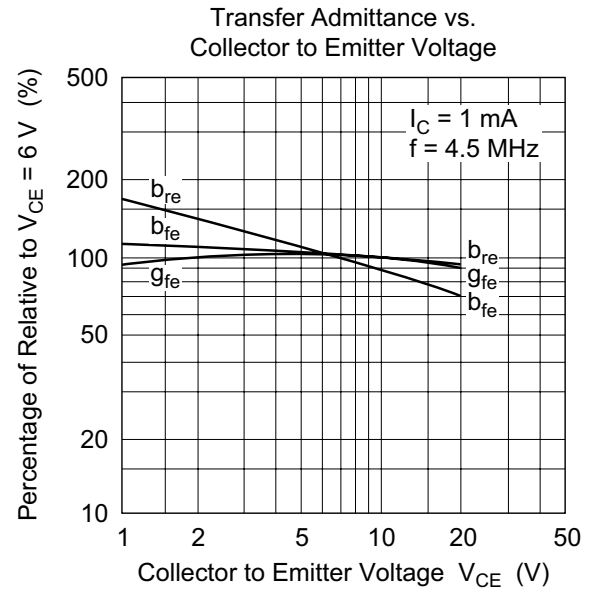
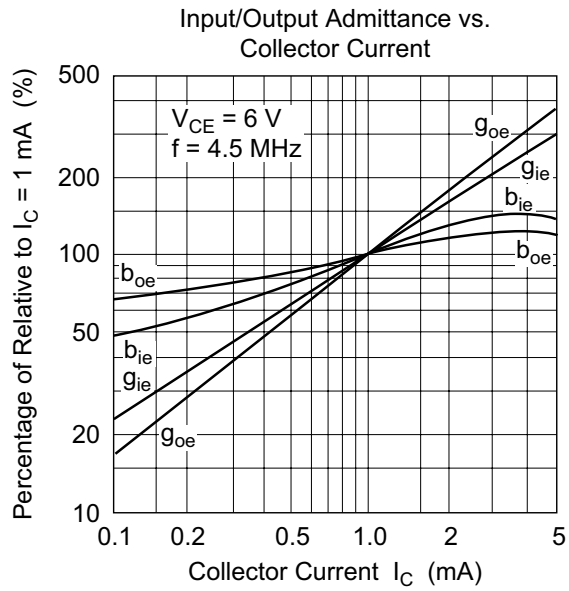
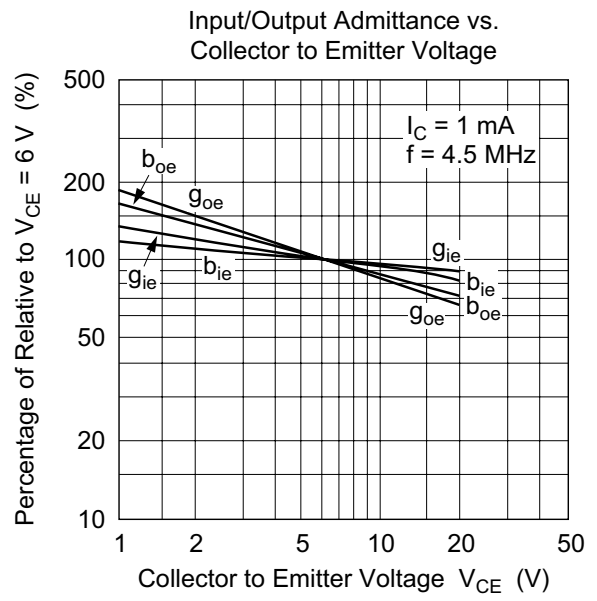
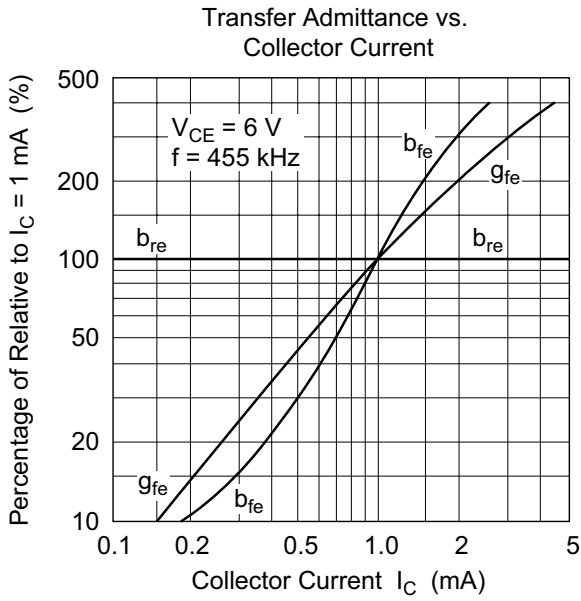
Small Signal y Parameters ($V_{CE} = 6\text{ V}$, $I_C = 1\text{ mA}$, Emitter Common)

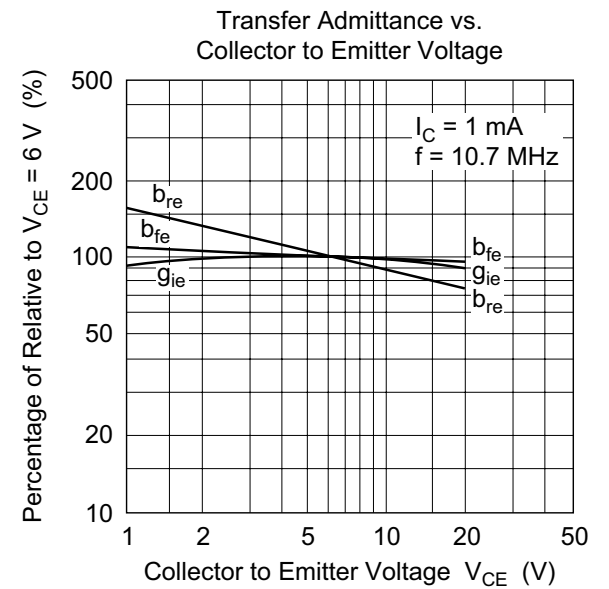
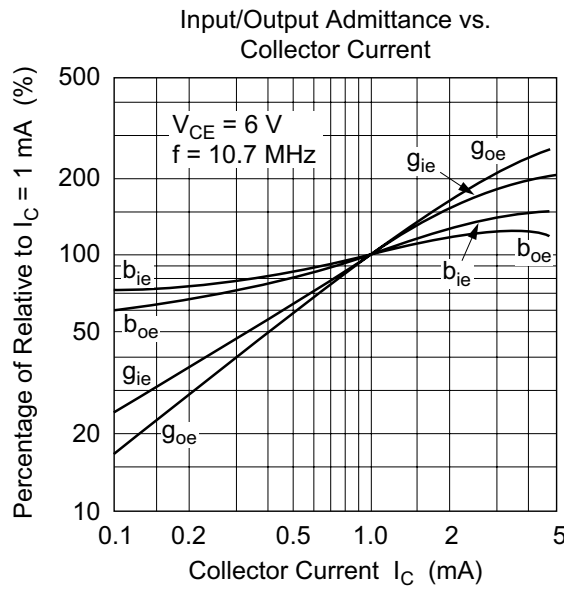
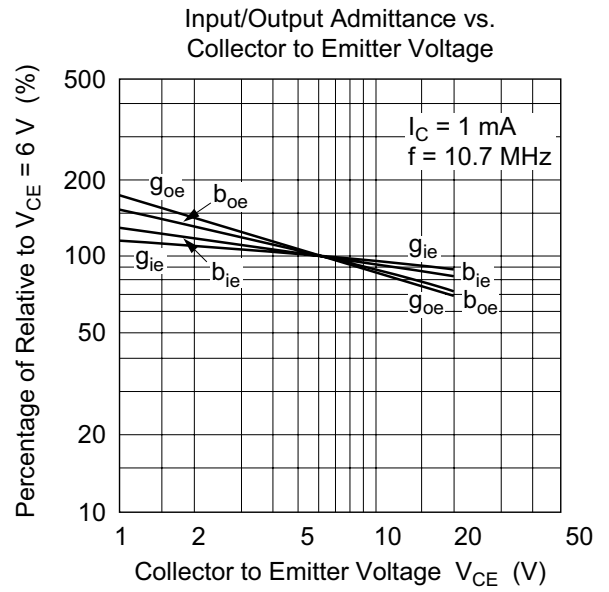
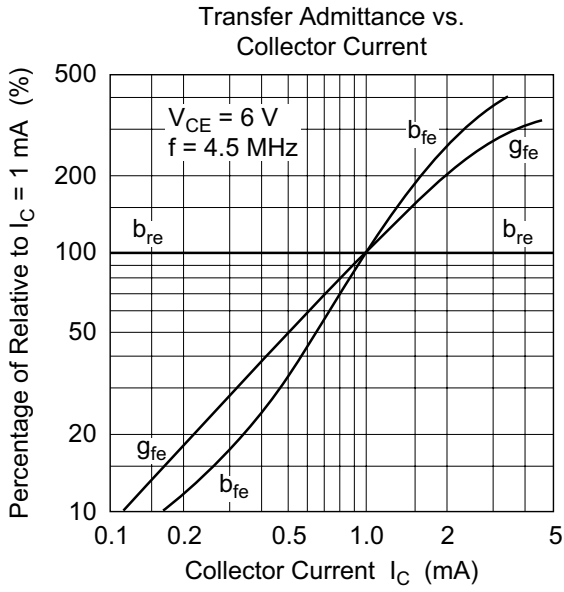
Item	Symbol	f	2SC460A, 2S461A	2SC460B, 2SC461B	2SC460C, 2SC461C	Unit
Input admittance	yie	455 kHz	$0.58 + j0.074$	$0.42 + j0.068$	$0.30 + j0.051$	mS
		4.5 MHz	$0.65 + j0.79$	$0.50 + j0.7$	$0.35 + j0.57$	
		10.7 MHz	$0.91 + j2.0$	$0.61 + j1.9$	$0.39 + j1.3$	
		100 MHz	$7.4 + j14$	$5.6 + j12$	$3.8 + j6.0$	
Reverse transfer admittance	yre	455 kHz	$-j0.003$	$-j0.003$	$-j0.003$	mS
		4.5 MHz	$-j0.04$	$-j0.04$	$-j0.04$	
		10.7 MHz	$-j0.13$	$-j0.13$	$-j0.13$	
		100 MHz	$-j1.0$	$-j1.0$	$-j1.0$	
Forward transfer admittance	yfe	455 kHz	$38 - j0.1$	$37 - j0.1$	$37 - j0.2$	mS
		4.5 MHz	$35 - j1.0$	$35 - j1.2$	$34 - j1.8$	
		10.7 MHz	$34 - j2.5$	$34 - j2.5$	$33 - j4.5$	
		100 MHz	$28 - j20$	$28 - j19$	$20 - j19$	
Output admittance	yoe	455 kHz	$0.0098 + j0.009$	$0.013 + j0.009$	$0.016 + j0.012$	mS
		4.5 MHz	$0.02 + j0.09$	$0.023 + j0.092$	$0.03 + j0.10$	
		10.7 MHz	$0.11 + j0.4$	$0.11 + j0.4$	$0.12 + j0.4$	
		100 MHz	$0.40 + j1.7$	$0.50 + j2.0$	$0.83 + j2.0$	

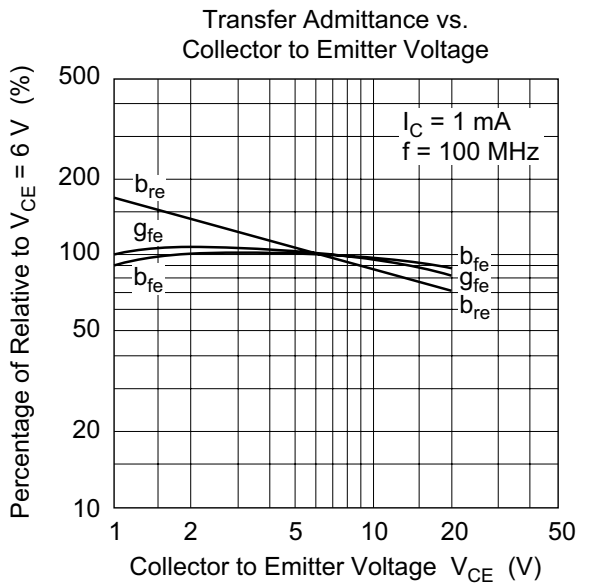
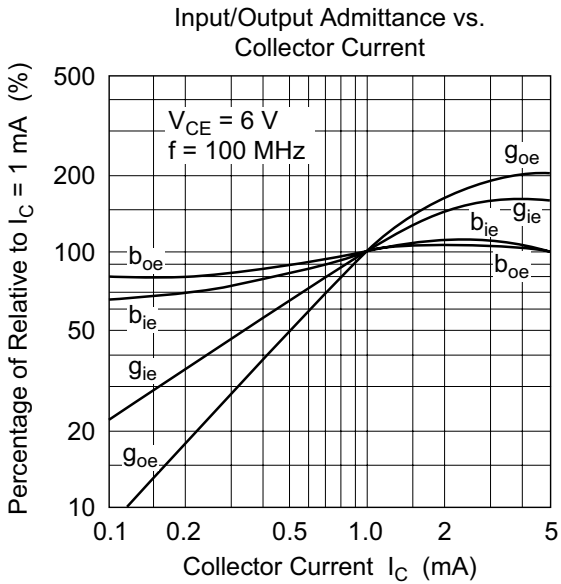
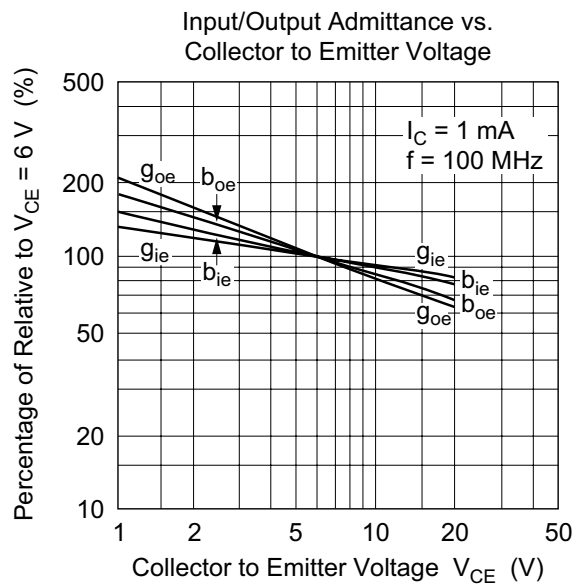
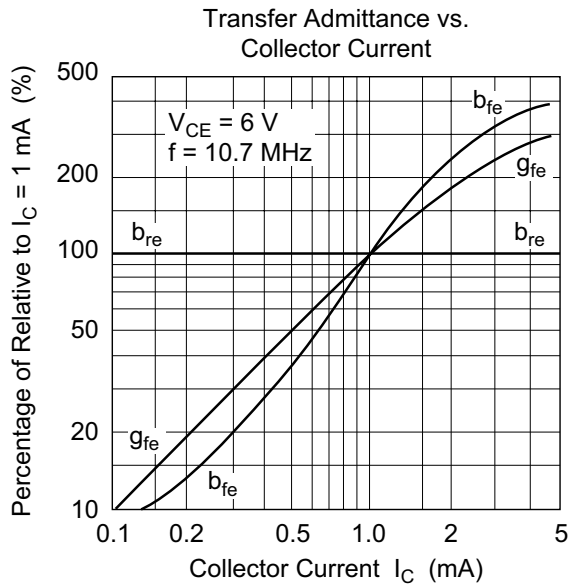


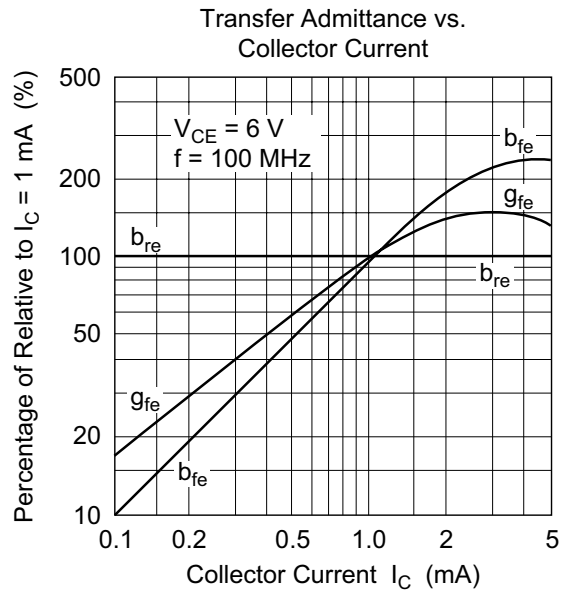




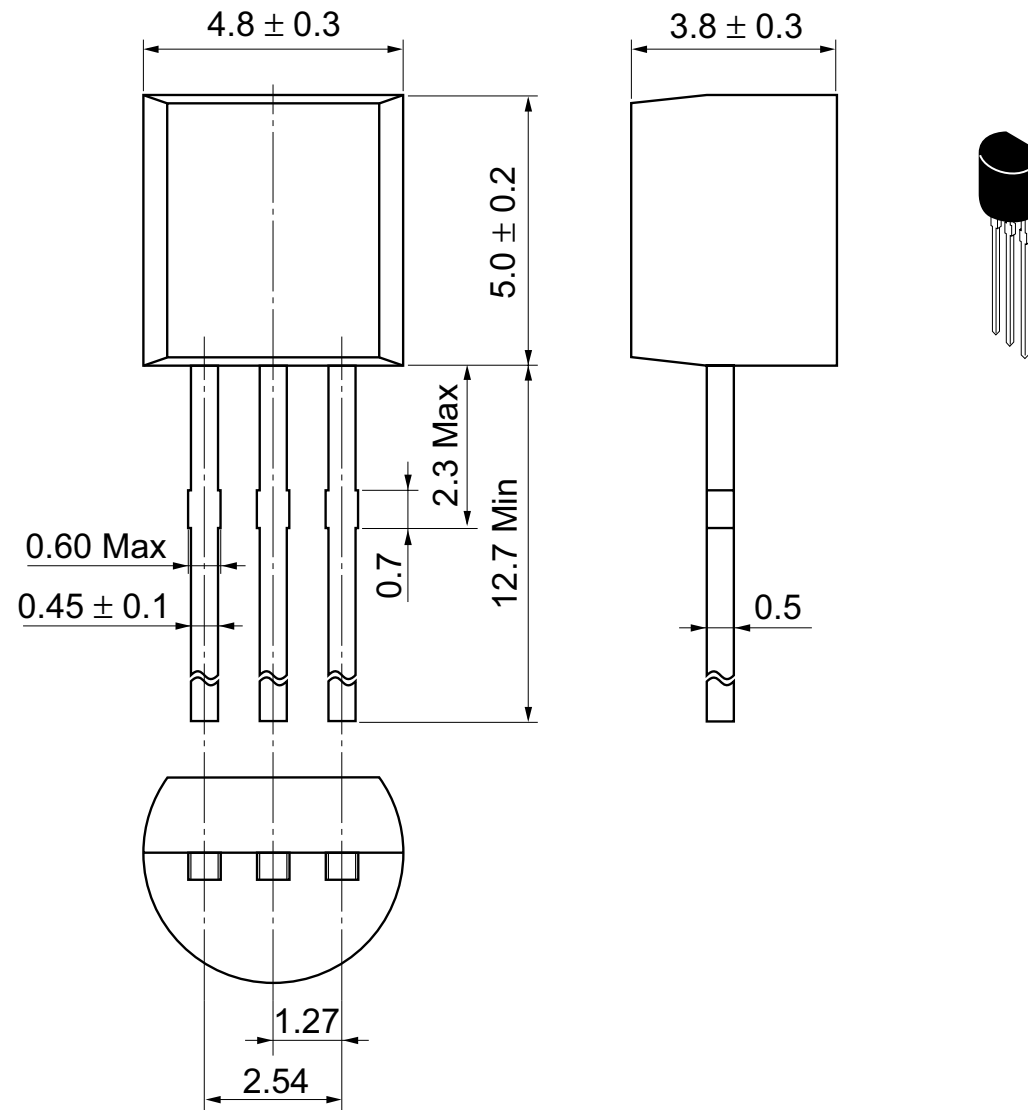








Unit: mm



Hitachi Code	TO-92 (2)
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	0.25 g

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